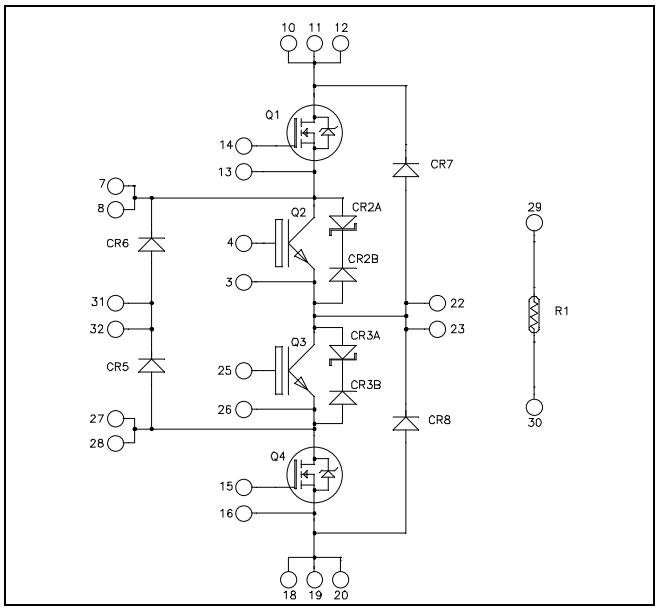
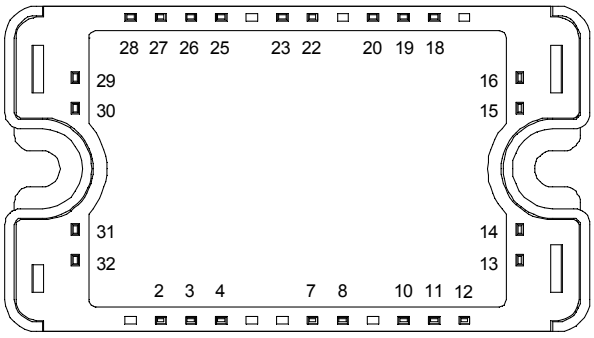
APTCV90TL12T3G

Three level inverter
CoolMOS & Trench + Field Stop IGBT4
Power Module

Trench & Field Stop IGBT4 Q2, Q3:
V_{CES} = 1200V ; I_C = 40A @ Tc = 80°C

CoolMOS™ Q1, Q4:
V_{DSS} = 900V ; I_D = 23A @ Tc = 80°C





All multiple inputs and outputs must be shorted together
Example: 10/11/12 ; 7/8 …

Application

- Solar converter
- Uninterruptible Power Supplies

Features

- ***Q2, Q3 Trench + Field Stop IGBT 4 Technology***
  - Low voltage drop
  - Low leakage current
  - Low switching losses
- ***Q1, Q4 CoolMOS™***
  - Ultra low R_{DSon}
  - Low Miller capacitance
  - Ultra low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

All ratings @ T_j = 25°C unless otherwise specified

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.
See application note APT0502 on www.microsemi.com

Q1 & Q4 Absolute maximum ratings (per CoolMOS™)

Symbol	Parameter		Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage		900	V
I_D	Continuous Drain Current	T_c = 25°C	30	A
		T_c = 80°C	23	
I_{DM}	Pulsed Drain current		75	
V_{GS}	Gate - Source Voltage		±20	V
R_{DSon}	Drain - Source ON Resistance		120	mΩ
P_D	Maximum Power Dissipation	T_c = 25°C	250	W
I_{AR}	Avalanche current (repetitive and non repetitive)		8.8	A
E_{AR}	Repetitive Avalanche Energy		2.9	mJ
E_{AS}	Single Pulse Avalanche Energy		1940	

Q1 & Q4 Electrical Characteristics (per CoolMOS™)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0V, V_{DS} = 900V	T_j = 25°C			100	µA
		V_{GS} = 0V, V_{DS} = 900V	T_j = 125°C		500		
$R_{DS(on)}$	Drain – Source on Resistance	V_{GS} = 10V, I_D = 26A			100	120	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 3mA		2.5	3	3.5	V
I_{GSS}	Gate – Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0V				100	nA

Q1 & Q4 Dynamic Characteristics (per CoolMOS™)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	V_{GS} = 0V ; V_{DS} = 100V f = 1MHz		6800		pF
C_{oss}	Output Capacitance			330		
Q_g	Total gate Charge	V_{GS} = 10V V_{Bus} = 400V I_D = 26A		270		nC
Q_{gs}	Gate – Source Charge			32		
Q_{gd}	Gate – Drain Charge			115		
$T_{d(on)}$	Turn-on Delay Time	**Inductive Switching (125°C)** V_{GS} = 10V V_{Bus} = 400V I_D = 26A R_G = 7.5Ω		70		ns
T_r	Rise Time			20		
$T_{d(off)}$	Turn-off Delay Time			400		
T_f	Fall Time			25		
R_{thJC}	Junction to Case Thermal resistance				0.5	°C/W

Q2 & Q3 Absolute maximum ratings (per IGBT)

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
I_C	Continuous Collector Current	T_C = 25°C	60	A
		T_C = 80°C	40	
I_{CM}	Pulsed Collector Current	T_C = 25°C	70	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_C = 25°C	220	W
RBSOA	Reverse Bias Safe Operating Area	T_j = 150°C	70A @ 1100V	

Q2 & Q3 Electrical Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V, V_{CE} = 1200V				250	µA
$V_{CE(sat)}$	Collector Emitter saturation Voltage	V_{GE} = 15V I_C = 35A	T_j = 25°C		1.85	2.25	V
			T_j = 150°C		2.25		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE} , I_C = 1.2mA		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				400	nA

Q2 & Q3 Dynamic Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
C_{ies}	Input Capacitance	V_{GE} = 0V V_{CE} = 25V f = 1MHz			1950		pF
C_{oes}	Output Capacitance				155		
C_{res}	Reverse Transfer Capacitance				115		
Q_G	Gate charge	V_{GE}= ±15V ; V_{CE}=600V I_C=35A			0.27		µC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = ±15V V_{CE} = 600V I_C = 35A R_G = 12Ω			130		ns
T_r	Rise Time				20		
$T_{d(off)}$	Turn-off Delay Time				300		
T_f	Fall Time				45		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) V_{GE} = ±15V V_{CE} = 600V I_C = 35A R_G = 12Ω			150		ns
T_r	Rise Time				35		
$T_{d(off)}$	Turn-off Delay Time				350		
T_f	Fall Time				80		
E_{on}	Turn-on Switching Energy	V_{GE} = ±15V V_{CE} = 600V I_C = 35A R_G = 12Ω	T_J = 25°C		2.6		mJ
			T_J = 150°C		4		
E_{off}	Turn-off Switching Energy		T_J = 25°C		2		mJ
			T_J = 150°C		3		
I_{sc}	Short Circuit data	V_{GE} ≤15V ; V_{Bus} = 900V t_p ≤10µs ; T_j = 150°C			140		A
R_{thJC}	Junction to Case Thermal Resistance					0.68	°C/W

CR2 & CR3 diode ratings and characteristics (per device)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_F	Diode + tranzorb Forward Voltage	I_F = 10A		10.5		V
R_{thJC}	Junction to Case Thermal Resistance				8	°C/W

CR5 & CR6 diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1000			V
I_{RM}	Maximum Reverse Leakage Current	V_R=1000V				100	µA
I_F	DC Forward Current		Tc = 80°C		40		A
V_F	Diode Forward Voltage	I_F = 40A			2.5	3	
		I_F = 80A			3.1		V
		I_F = 40A	T_j = 125°C		2		
t_{rr}	Reverse Recovery Time	I_F = 40A V_R = 667V di/dt =200A/µs	T_j = 25°C		250		ns
			T_j = 125°C		315		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		415		nC
			T_j = 125°C		1650		
E_{rr}	Reverse Recovery Energy	I_F = 40A V_R = 667V di/dt =1000A/µs	T_j = 125°C		1.3		mJ
R_{thJC}	Junction to Case Thermal Resistance					1.2	°C/W

CR7 & CR8 diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	V_R=1200V				100	µA
I_F	DC Forward Current		Tc = 80°C		40		A
V_F	Diode Forward Voltage	I_F = 30A			2.6	3.1	
		I_F = 60A			3.2		V
		I_F = 30A	T_j = 125°C		1.8		
t_{rr}	Reverse Recovery Time	I_F = 30A V_R = 800V di/dt =200A/µs	T_j = 25°C		300		ns
			T_j = 125°C		380		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		360		nC
			T_j = 125°C		1700		
E_{rr}	Reverse Recovery Energy	I_F = 30A V_R = 800V di/dt =1000A/µs	T_j = 125°C		1.6		mJ
R_{thJC}	Junction to Case Thermal Resistance					1.2	°C/W

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	T_{25} = 298.15 K			3952		K
ΔB/B		T_C=100°C		4		%

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

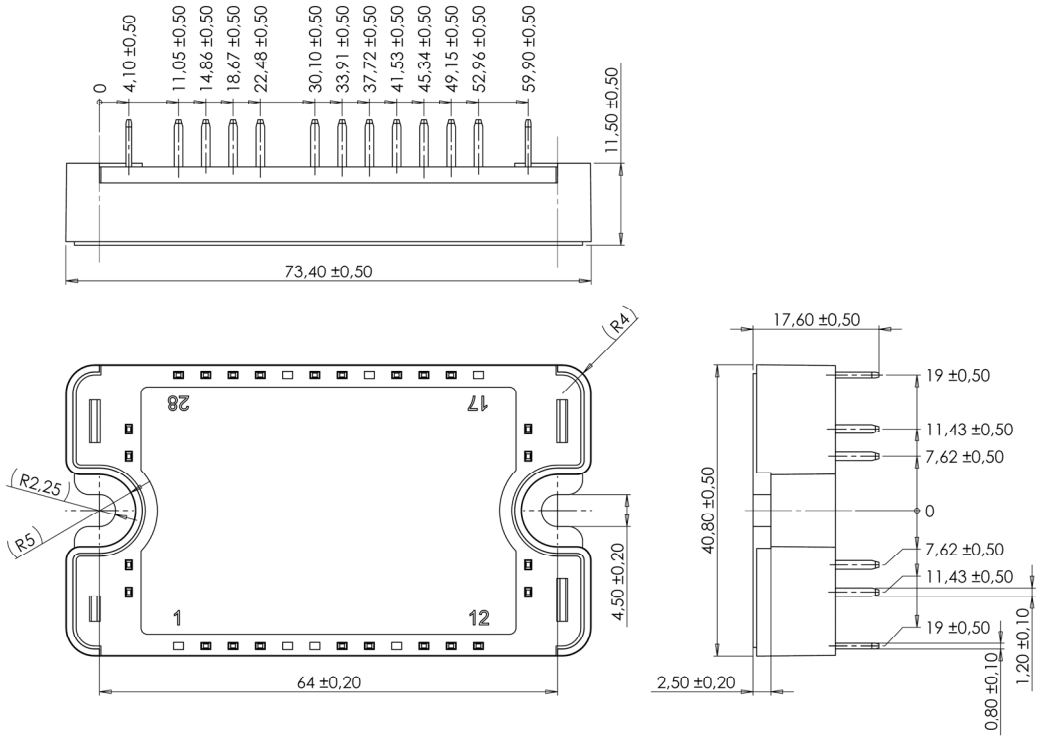
T: Thermistor temperature
R_T: Thermistor value at T

Thermal and package characteristics

Symbol	*Characteristic*			*Min*	*Typ*	*Max*	*Unit*
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_J	Operating junction temperature range			-40		175*	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					110	g

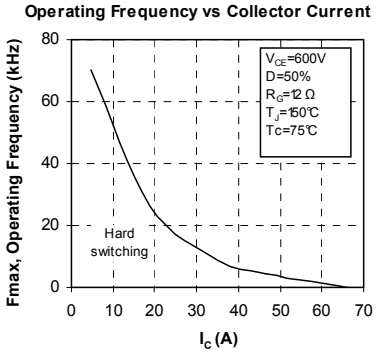
* Tjmax = 150°C for Q1 & Q4

SP3 Package outline (dimensions in mm)

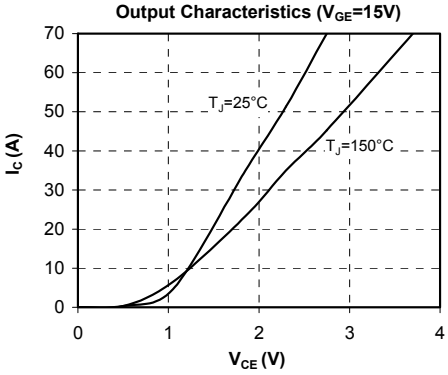


See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

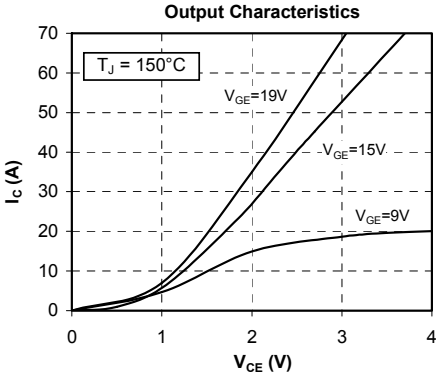
Q2 & Q3 Typical performance curve



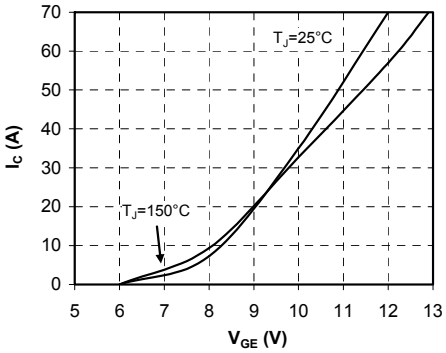
Output Characteristics (V_{GE}=15V)



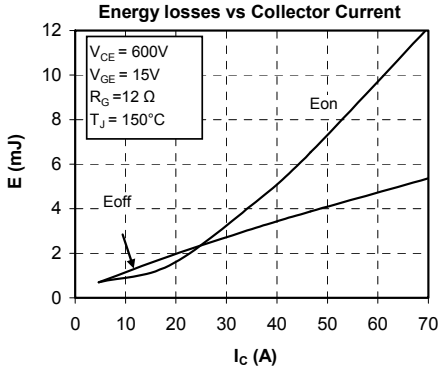
Output Characteristics



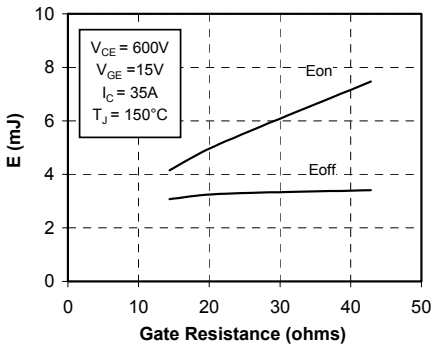
Transfert Characteristics



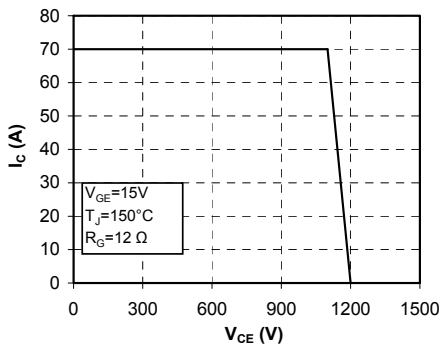
Energy losses vs Collector Current



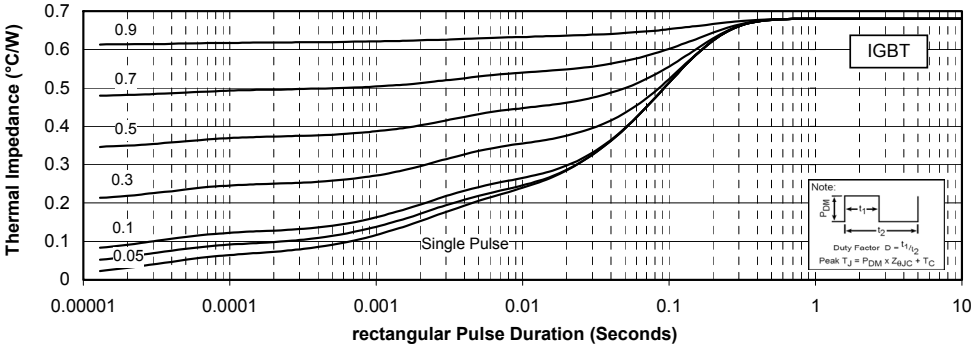
Switching Energy Losses vs Gate Resistance



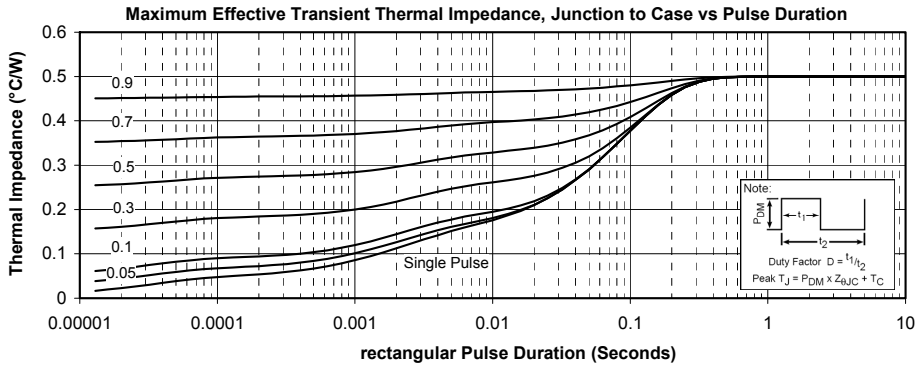
Reverse Bias Safe Operating Area

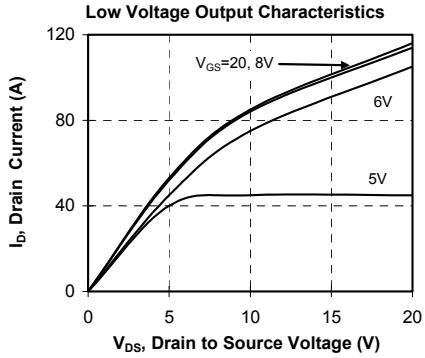


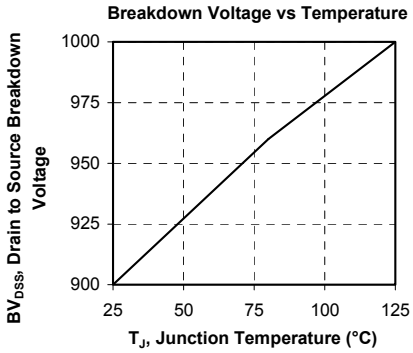
maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration

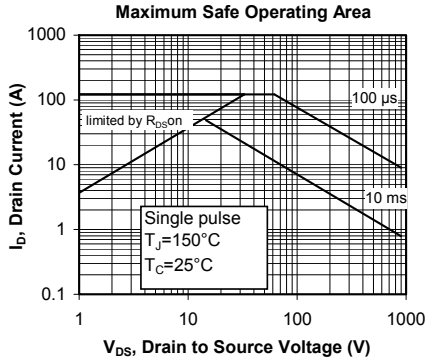


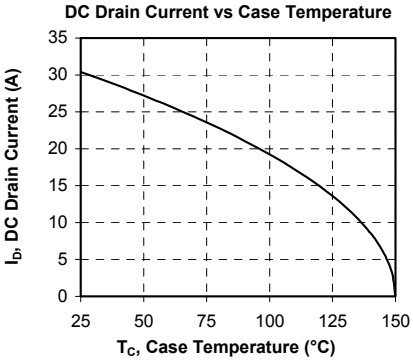
Q1 & Q4 Typical performance curve

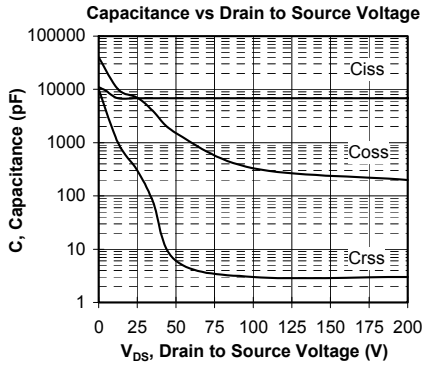


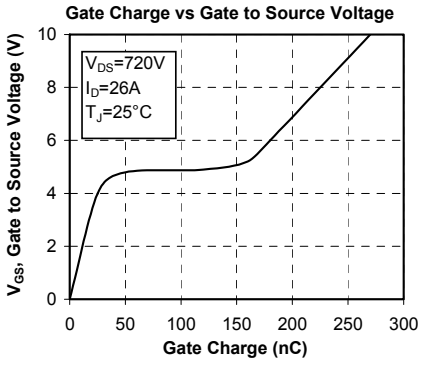




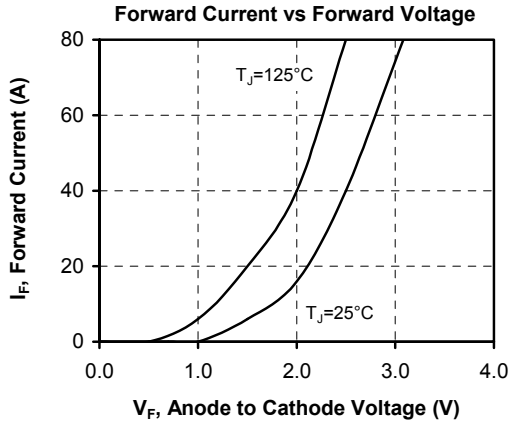


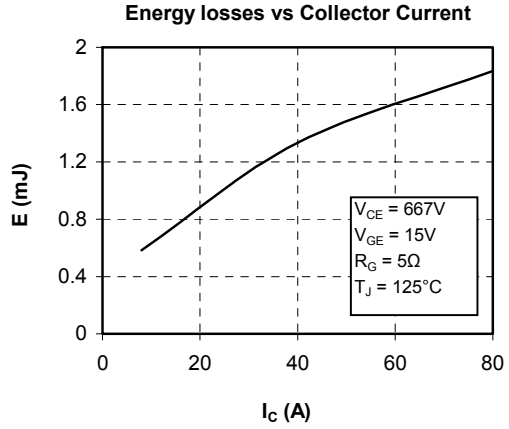


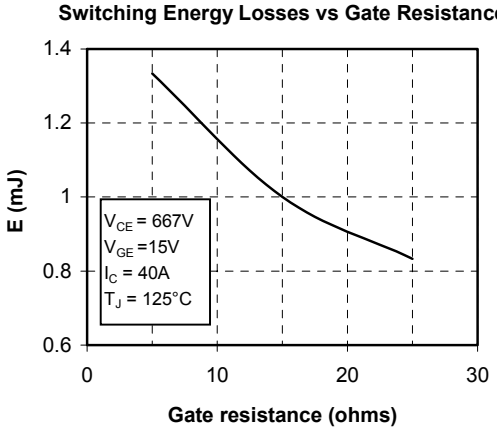


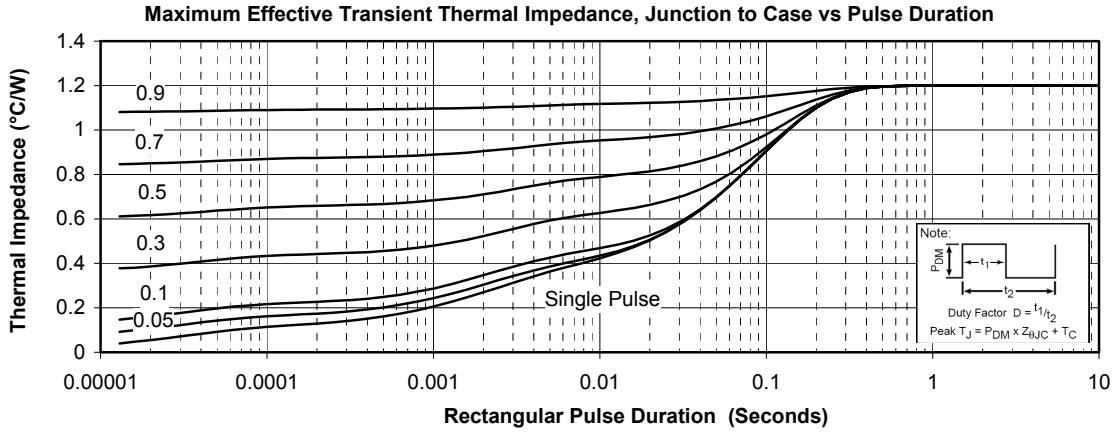


CR5 & CR6 Typical performance curve

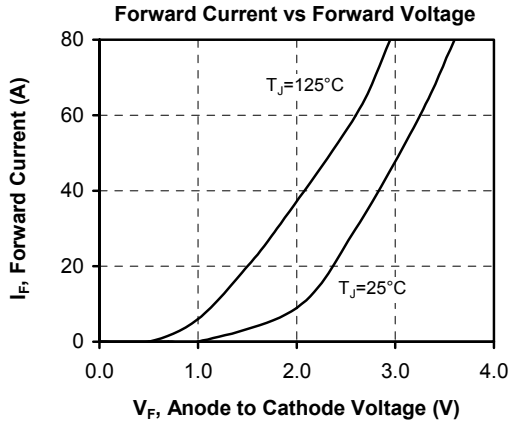


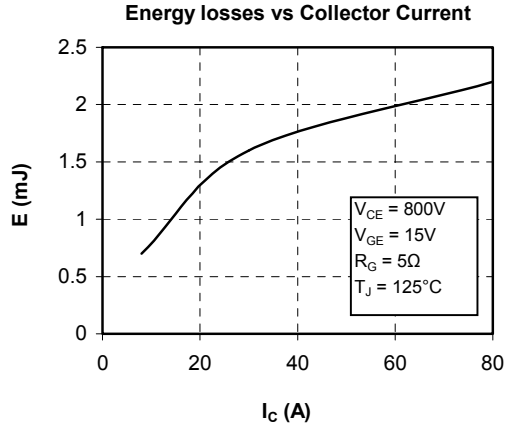


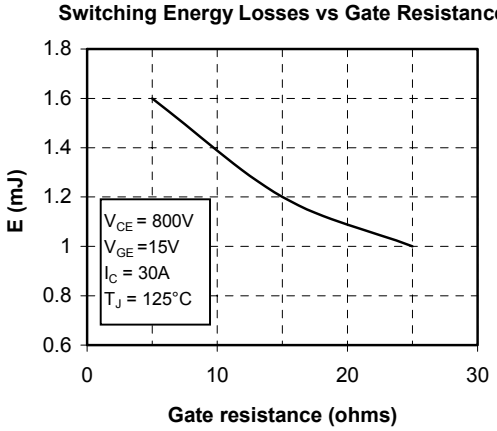


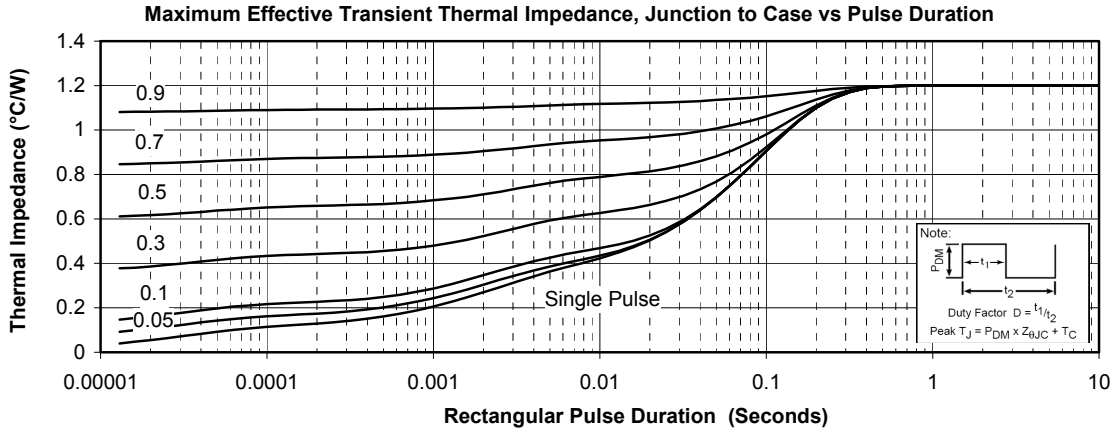


CR7 & CR8 Typical performance curve









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